4-Mbit (512K x 8) Static RAM

Features

- Very high speed: 45 ns
- Voltage range: 4.5V–5.5V
- Pin compatible with CY62148B
- Ultra low standby power
  - Typical standby current: 1 µA
  - Maximum standby current: 7 µA (Industrial)
- Ultra low active power
  - Typical active current: 2.0 mA @ f = 1 MHz
- Easy memory expansion with $\overline{CE}$, and $\overline{OE}$ features
- Automatic power down when deselected
- CMOS for optimum speed/power
- Available in Pb-free 32-pin SOIC and 32-pin TSOP II packages

Functional Description [1]

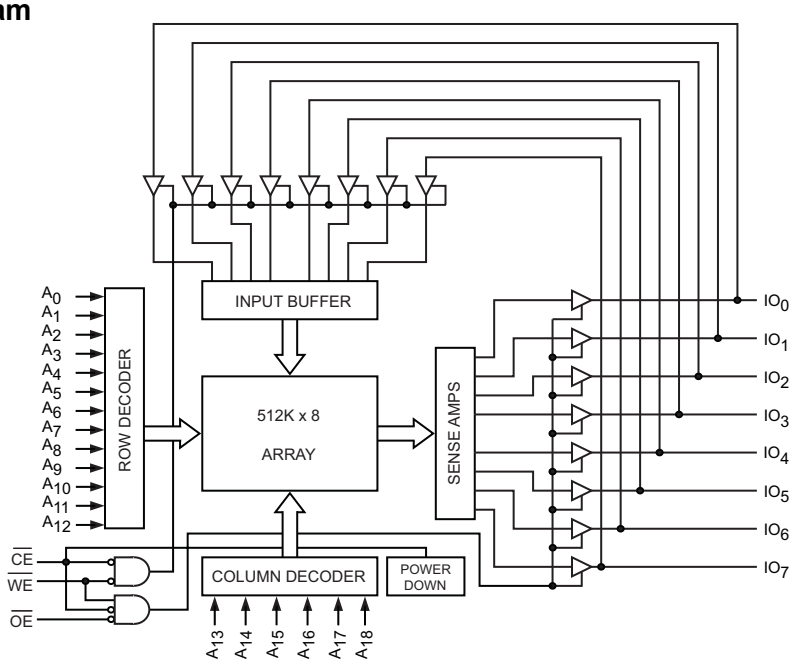
The CY62148E is a high performance CMOS static RAM organized as 512K words by 8 bits. This device features advanced circuit design to provide ultra low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power down feature that significantly reduces power consumption when addresses are not toggling. Placing the device into standby mode reduces power consumption by more than 99% when deselected ($\overline{CE}$ HIGH).

To write to the device, take Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. Data on the eight IO pins (IO_0 through IO_7) is then written into the location specified on the address pins (A_0 through A_{18}).

To read from the device, take Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing Write Enable ($\overline{WE}$) HIGH. Under these conditions, the contents of the memory location specified by the address pins appear on the IO pins.

The eight input and output pins (IO_0 through IO_7) are placed in a high impedance state when the device is deselected ($\overline{CE}$ HIGH), the outputs are disabled ($\overline{OE}$ HIGH), or during a write operation ($\overline{CE}$ LOW and $\overline{WE}$ LOW).

Logic Block Diagram

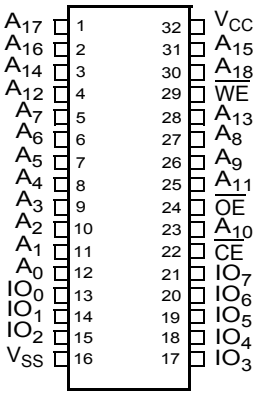


Note
1. For best practice recommendations, refer to the Cypress application note “System Design Guidelines” at http://www.cypress.com.

Pin Configuration [2]

32-pin SOIC/TSOP II Pinout

Top View



Product Portfolio

Product	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating I_{CC} (mA)				Standby I_{SB2} (µA)	
					f = 1MHz		f = f_{max}			
	Min	Typ [3]	Max		Typ [3]	Max	Typ [3]	Max	Typ [3]	Max
CY62148E-45LL	4.5	5.0	5.5	45 ns	2	2.5	15	20	1	7
CY62148E-55LL [4]	4.5	5.0	5.5	55 ns	2	3	15	25	1	20

Shaded areas contain preliminary information.

Notes
2. NC pins are not connected on the die.
3. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ)}$, $T_A = 25°C$.
4. Automotive product information is Preliminary.

Maximum Ratings

Exceeding maximum ratings may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature ..... –65°C to + 150°C

Ambient Temperature with Power Applied..... –55°C to + 125°C

Supply Voltage to Ground Potential..... –0.5V to 6.0V ($V_{CC\ max}$ + 0.5V)

DC Voltage Applied to Outputs in High-Z State [5, 6]..... –0.5V to 6.0V ($V_{CC\ max}$ + 0.5V)

DC Input Voltage [5, 6]..... –0.5V to 6.0V ($V_{CC\ max}$ + 0.5V)

Output Current into Outputs (LOW)..... 20 mA

Static Discharge Voltage..... > 2001V (per MIL-STD-883, Method 3015)

Latch-up Current..... > 200 mA

Operating Range

Device	Range	Ambient Temperature	V_{CC} [7]	Speed
CY62148E	Industrial	–40°C to +85°C	4.5V to 5.5V	45 ns
	Automotive	–40°C to +125°C		55 ns

Electrical Characteristics (Over the Operating Range)

Parameter	Description	Test Conditions		45 ns (Industrial)			55 ns (Automotive)			Unit
				Min	Typ [3]	Max	Min	Typ [3]	Max	
V_{OH}	Output HIGH Voltage	I_{OH} = –1 mA		2.4			2.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 2.1 mA				0.4			0.4	V
V_{IH}	Input HIGH Voltage	V_{CC} = 4.5V to 5.5V		2.2		V_{CC} + 0.5	2.2		V_{CC} + 0.5	V
V_{IL}	Input LOW voltage	V_{CC} = 4.5V to 5.5V	For TSOPII package	–0.5		0.8	–0.5		0.8	V
			For SOIC package	–0.5		0.6 [8]	–0.5		0.6 [8]	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1		+1	–4		+4	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		–1		+1	–4		+4	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{max} = $1/t_{RC}$	V_{CC} = V_{CCmax}, I_{OUT} = 0 mA CMOS levels		15	20		15	25	mA
		f = 1 MHz			2	2.5		2	3	
I_{SB2}	Automatic CE Power down Current — CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC} = V_{CCmax}			1	7		1	20	µA

Capacitance (For All Packages) [9]

Parameter	Description	Test Conditions	Max	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	10	pF
C_{OUT}	Output Capacitance		10	pF

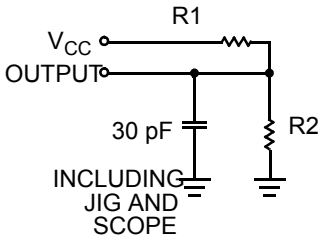
Notes

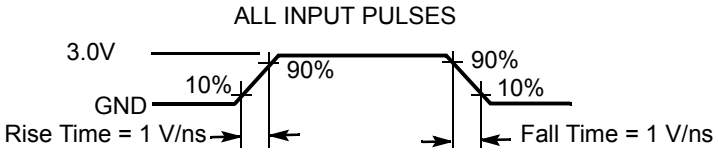
5. $V_{IL(min)}$ = –2.0V for pulse durations less than 20 ns for I ≤ 30 mA.
6. $V_{IH(max)}$ = V_{CC}+0.75V for pulse durations less than 20 ns.
7. Full device AC operation assumes a minimum of 100 µs ramp time from 0 to V_{CC}(min) and 200 µs wait time after V_{CC} stabilization.
8. Under DC conditions the device meets a V_{IL} of 0.8V. However, in dynamic conditions Input LOW Voltage applied to the device must not be higher than 0.6V. This is applicable to SOIC package only. Refer to AN13470 for details.
9. Tested initially and after any design or process changes that may affect these parameters.

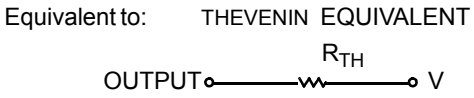
Thermal Resistance [9]

Parameter	Description	Test Conditions	SOIC Package	TSOP II Package	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 × 4.5 inch, 2-layer printed circuit board	75	77	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		10	13	°C/W

AC Test Loads and Waveforms







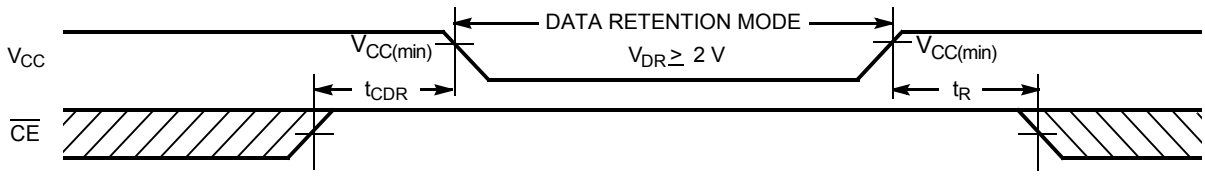
Parameters	5.0V	Unit
R1	1800	Ω
R2	990	Ω
R_{TH}	639	Ω
V_{TH}	1.77	V

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions		Min	Typ [3]	Max	Unit
V_{DR}	V_{CC} for Data Retention			2			V
I_{CCDR}	Data Retention Current	V_{CC}= V_{DR}, $\overline{CE} \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$	Ind'l		1	7	µA
			Auto		1	20	
t_{CDR} [9]	Chip Deselect to Data Retention Time			0			ns
t_R [10]	Operation Recovery Time			t_{RC}			ns

Shaded areas contain preliminary information.

Data Retention Waveform



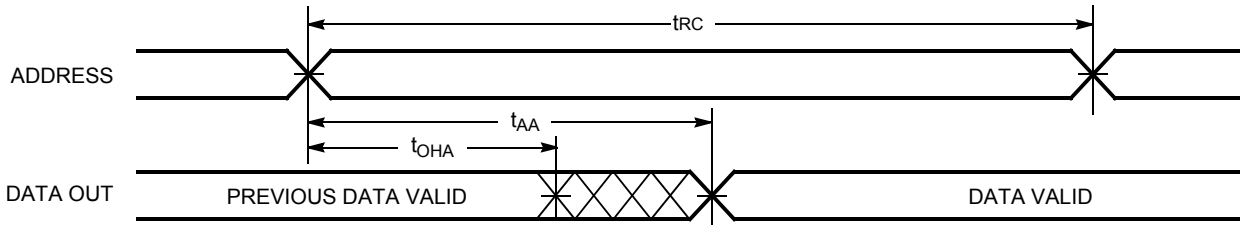
Note
10. Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min)} \geq 100$ µs or stable at $V_{CC(min)} \geq 100$ µs.

Switching Characteristics (Over the Operating Range) [11]

Parameter	Description	45 ns (Industrial)		55 ns (Automotive)		Unit
		Min	Max	Min	Max	
Read Cycle						
t_{RC}	Read Cycle Time	45		55		ns
t_{AA}	Address to Data Valid		45		55	ns
t_{OHA}	Data Hold from Address Change	10		10		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		45		55	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		22		25	ns
t_{LZOE}	$\overline{OE}$ LOW to LOW Z [12]	5		5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z [12, 13]		18		20	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z [12]	10		10		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z [12, 13]		18		20	ns
t_{PU}	$\overline{CE}$ LOW to Power up	0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power down		45		55	ns
Write Cycle [14]						
t_{WC}	Write Cycle Time	45		55		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	35		35		ns
t_{AW}	Address Setup to Write End	35		35		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Setup to Write Start	0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	35		35		ns
t_{SD}	Data Setup to Write End	25		25		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z [12, 13]		18		20	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z [12]	10		10		ns

Switching Waveforms

Read Cycle 1 (Address Transition Controlled) [15, 16]

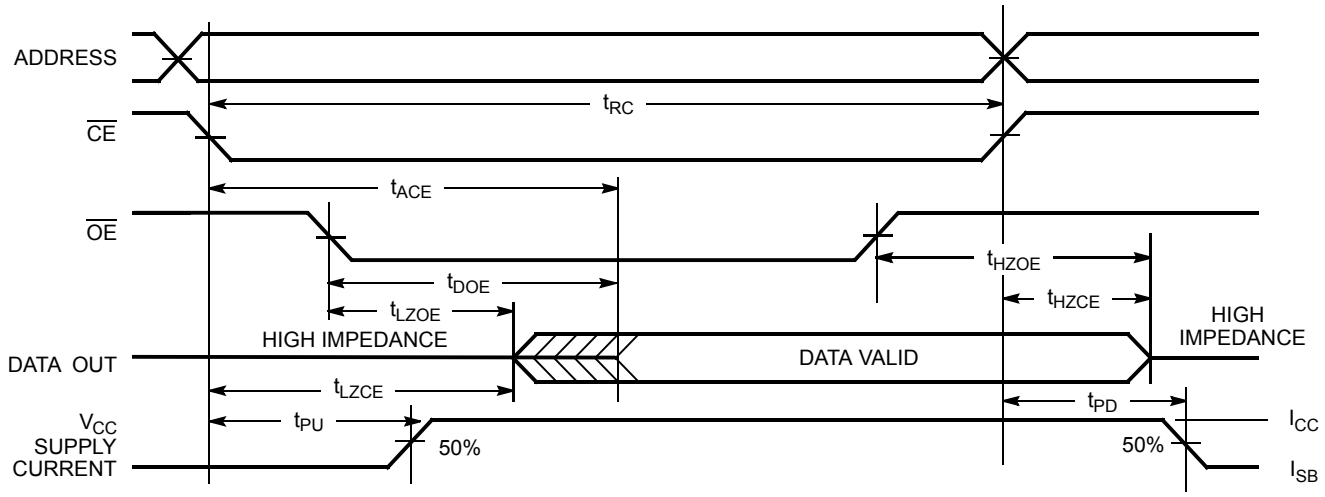


Notes

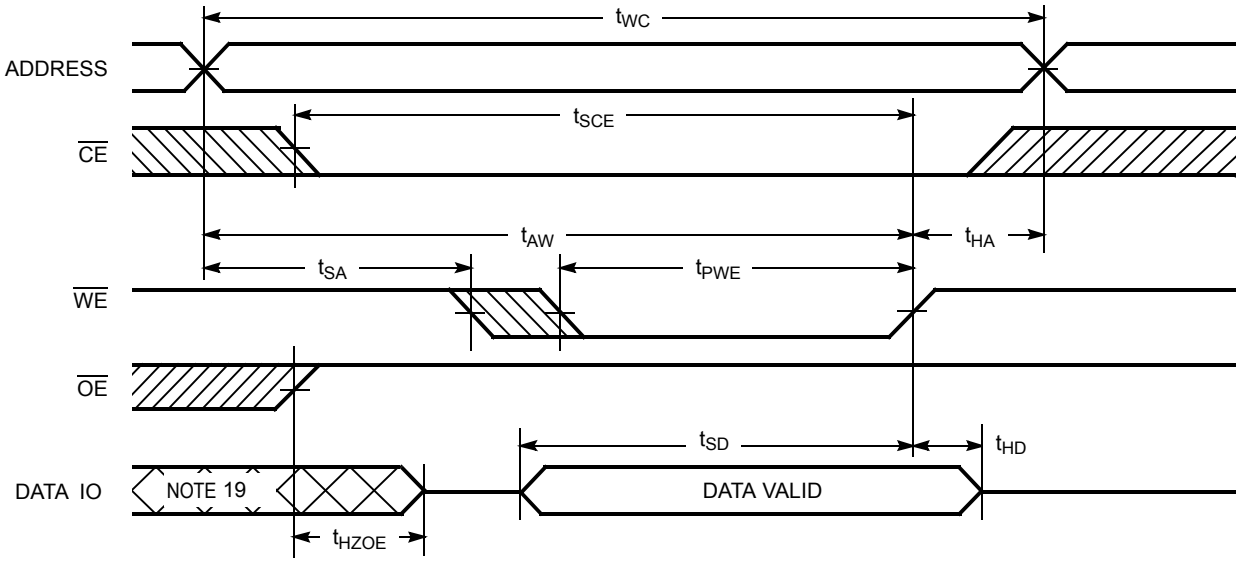
11. Test conditions for all parameters other than tri-state parameters assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3V, and output loading of the specified I_{OL}/I_{OH} as shown in the "AC Test Loads and Waveforms" on page 4.
12. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
13. t_{HZOE}, t_{HZCE}, and t_{HZWE} transitions are measured when the outputs enter a high-impedance state.
14. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing should be referenced to the edge of the signal that terminates the write.
15. The device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}.
16. $\overline{WE}$ is HIGH for read cycles.

Switching Waveforms (continued)

Read Cycle No. 2 ($\overline{OE}$ Controlled) [15, 17]



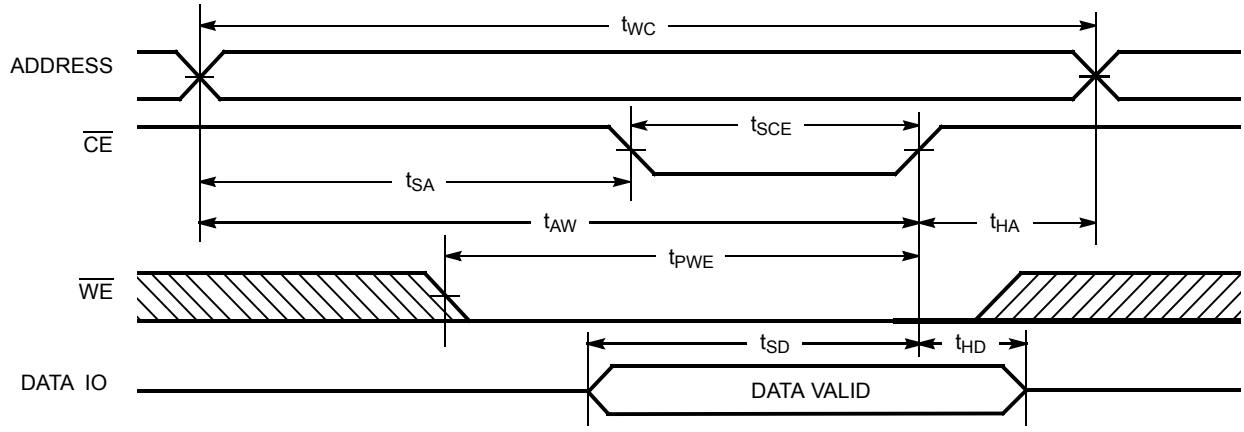
Write Cycle No. 1 ($\overline{WE}$ Controlled, $\overline{OE}$ HIGH During Write) [13, 17, 18]



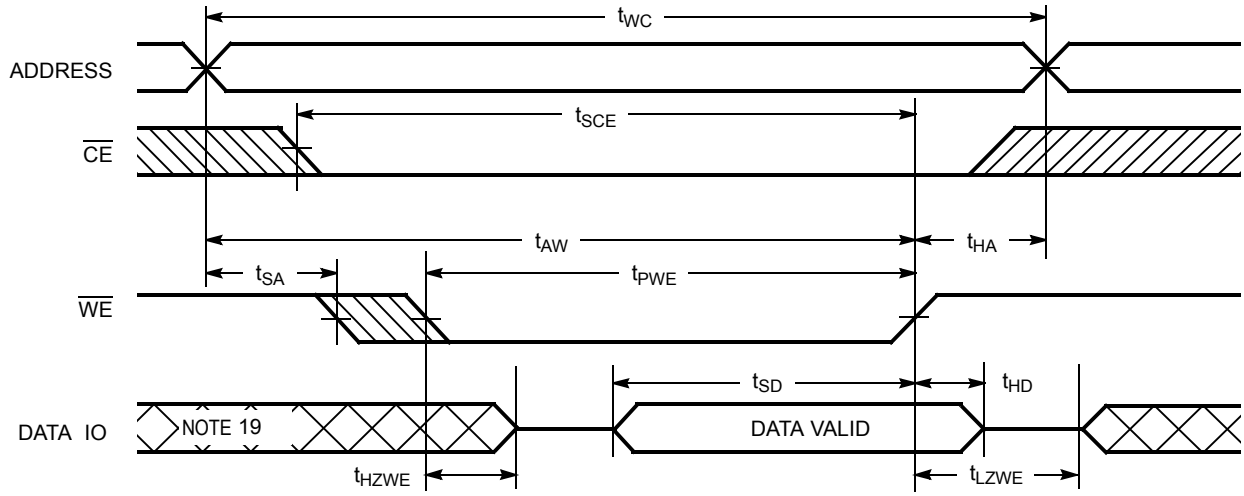
Notes
17. Address valid prior to or coincident with $\overline{CE}$ transition LOW.
18. Data IO is high impedance if $\overline{OE}$ = V_{IH}.
19. During this period, the IOs are in output state and input signals must not be applied.

Switching Waveforms (continued)

Write Cycle No. 2 ($\overline{CE}$ Controlled) [14, 18, 20]



Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW) [20]



Truth Table

$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	IO's	Mode	Power
H	X	X	High Z	Deselect/Power down	Standby (I_{SB})
L	H	L	Data Out	Read	Active (I_{CC})
L	L	X	Data In	Write	Active (I_{CC})
L	H	H	High Z	Selected, Outputs Disabled	Active (I_{CC})

Note
20. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ = V_{IH}, the output remains in a high impedance state.

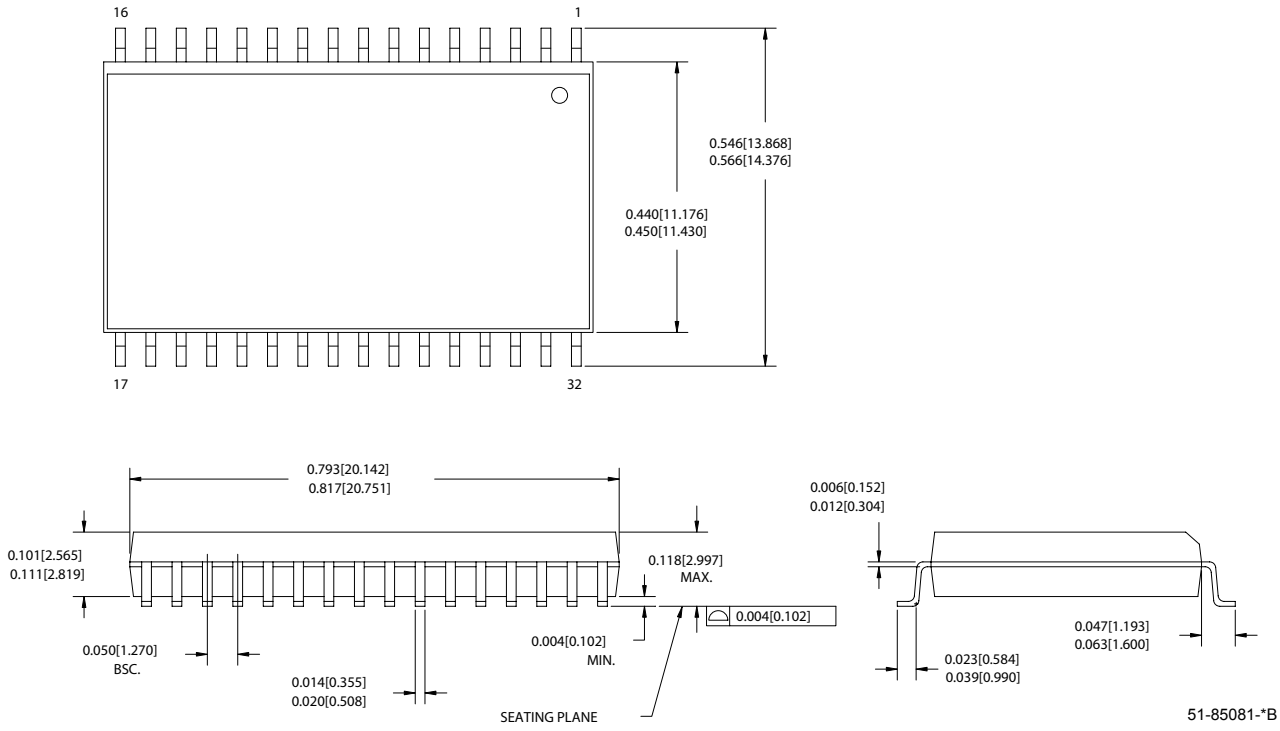
Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62148ELL-45SXI	51-85081	32-pin Small Outline Integrated Circuit (Pb-free)	Industrial
	CY62148ELL-45ZSXI	51-85095	32-pin Thin Small Outline Package II (Pb-free)	
55	CY62148ELL-55SXE	51-85081	32-pin Small Outline Integrated Circuit (Pb-free)	Automotive
	CY62148ELL-55ZSXE	51-85095	32-pin Thin Small Outline Package II (Pb-free)	

Shaded areas contain preliminary information. Contact your local Cypress sales representative for availability of these parts.

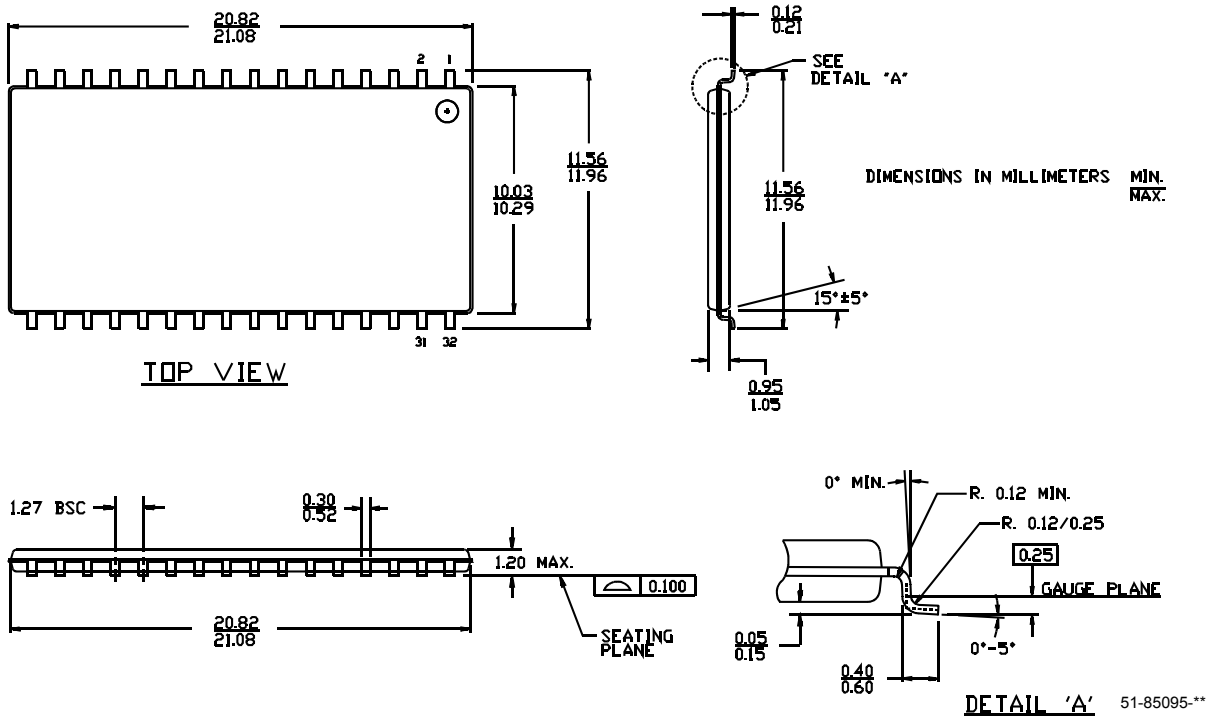
Package Diagrams

Figure 1. 32-pin (450 MIL) Molded SOIC, 51-85081



Package Diagrams (continued)

Figure 2. 32-pin TSOP II, 51-85095



Document History Page

Document Title: CY62148E MoBL®, 4-Mbit (512K x 8) Static RAM Document Number: 38-05442				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	201580	01/08/04	AJU	New Data Sheet
*A	249276	See ECN	SYT	Changed from Advance Information to Preliminary Moved Product Portfolio to Page 2 Added RTSOP II and Removed FBGA Package Changed V_{CC} stabilization time in footnote #7 from 100 μs to 200 μs Changed I_{CCDR} from 2.0 μA to 2.5 μA Changed typo in Data Retention Characteristics(t_R) from 100 μs to t_{RC} ns Changed t_{OHA} from 6 ns to 10 ns for both 35 ns and 45 ns Speed Bin Changed t_{HZOE}, t_{HZWE} from 12 to 15 ns for 35 ns Speed Bin and 15 to 18 ns for 45 ns Speed Bin Changed t_{SCE} from 25 to 30 ns for 35 ns Speed Bin and 40 to 35 ns for 45 ns Speed Bin Changed t_{HZCE} from 12 to18 ns for 35 ns Speed Bin and 15 to 22 ns for 45 ns Speed Bin Changed t_{SD} from 15 to 18 ns for 35 ns Speed Bin and 20 to 22 ns for 45 ns Speed Bin Changed t_{DOE} from 15 to 18 ns for 35 ns Speed Bin Corrected typo in Package Name Changed Ordering Information to include Pb-Free Packages
*B	414820	See ECN	ZSD	Changed from Preliminary to Final Changed the address of Cypress Semiconductor Corporation on Page #1 from “3901 North First Street” to “198 Champion Court” Removed 35ns Speed Bin Removed “L” version of CY62148E Changed I_{CC} (Typ) value from 1.5 mA to 2 mA at f=1 MHz Changed I_{CC} (Max) value from 2 mA to 2.5 mA at f=1 MHz Changed I_{CC} (Typ) value from 12 mA to 15 mA at f=f_{max} Removed I_{SB1} spec from the Electrical characteristics table Changed I_{SB2} Typ values from 0.7 μA to 1 μA and Max values from 2.5 μA to 7 μA Modified footnote #4 to include current limit Removed redundant footnote on DNU pins Changed the AC testload capacitance from 100 pF to 30 pF on page #4 Changed test load parameters R1, R2, R_{TH} and V_{TH} from 1838 Ω, 994 Ω, 645 Ω and 1.75V to 1800 Ω, 990 Ω, 639 Ω and 1.77V Changed I_{CCDR} from 2.5 μA to 7 μA Added I_{CCDR} typical value Changed t_{LZOE} from 3 ns to 5 ns Changed t_{LZCE} and t_{LZWE} from 6 ns to 10 ns Changed t_{HZCE} from 22 ns to 18 ns Changed t_{PWE} from 30 ns to 35 ns Changed t_{SD} from 22 ns to 25 ns Updated the ordering information table and replaced Package Name column with Package Diagram
*C	464503	See ECN	NXR	Included Automotive Range in product offering Updated the Ordering Information
*D	485639	See ECN	VKN	Corrected the operating range to 4.5V - 5.5V on page# 3
*E	833080	See ECN	VKN	Added footnote #8 Added V_{IL}spec for SOIC package